OPA9445L

Infrared LED Chip

GaAlAs/GaAs

1. Material

Substrate	GaAs	(N Type)
Epitaxial Layer	GaAlAs	(P/N Type)

2. Electrode

N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbo	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F		1.5	1.55	V	IF=100mA
Reverse Voltage	V_R	8			V	IR=10uA
Power	P_O	20	25		mW	IF=100mA
Wavelength	λ_P		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : Power is measured by Sorter E/T system with bare chip.

4. Mechanical Data

(a) Emission Area	---------------------------	12.8mil	x	12.8mil
(b) Bottom Area	---------------------------	13.8mil	x	13.8mil
(c) Bonding Pad	---------------------------	150um		
(d) Chip Thickness	---------------------------	11mil		
(e) Junction Height	---------------------------	6.7mil